



2300MHz-2400MHz, 100W, 28V High Power RF LDMOS FETs

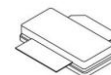
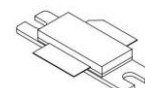
Description

The ITCH24100B2 is a 100-watt, internally matched LDMOS FET, designed for multicarrier WCDMA/PCS/DCS/LTE base station and ISM applications with frequencies from 2300 to 2400 MHz. It Can be used in Class AB/B and Class C for all typical cellular base station modulation formats.

•Typical Performance (On Innegration fixture with device soldered):

V_{DD} = 28 Volts, I_{DQ} = 900 mA, Pulse CW, Pulse Width=100 us, Duty cycle=20% .

Frequency	G _p (dB)	P _{-1dB} (dBm)	η _D @P ₋₁ (%)	P _{-3dB} (dBm)	η _D @P ₋₃ (%)
2300 MHz	18.2	50.8	52.8	51.5	54.2
2350 MHz	18.3	50.6	52.8	51.4	54.6
2400 MHz	18.7	50.1	51.8	51.0	54.0

ITCH24100B2**ITCH24100B2E**

•Typical Single-Carrier W-CDMA Performance (On Test Fixture with device soldered):

V_{DD}=28Volts, I_{DQ} = 900 mA, P_{out}= 41dBm Avg., IQ Magnitude Clipping, Channel Bandwidth = 3.84 MHz, Input Signal PAR = 10.5 dB @ 0.01% Probability on CCDF.

Frequency	P _{OUT} (dBm)	G _p (dB)	η _D (%)	ACPR _{5M} (dBc)
2300 MHz	41	17.4	20.5	-40.4
2350 MHz	41	17.8	20.9	-39.9
2400 MHz	41	18.2	21.7	-39.0

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Internally Matched for Ease of Use
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V _{DSS}	70	Vdc
Gate--Source Voltage	V _{GS}	-10 to +10	Vdc
Operating Voltage	V _{DD}	+32	Vdc
Storage Temperature Range	T _{stg}	-65 to +150	°C
Case Operating Temperature	T _c	+150	°C
Operating Junction Temperature	T _j	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case T _C = 85°C, T _J =200°C, DC test	R _{θJC}	0.45	°C/W

Table 3. ESD Protection Characteristics



Test Methodology	Class
Human Body Model (per JESD22--A114)	Class 2

Table 4. Electrical Characteristics (TA = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
DC Characteristics					
Drain-Source Breakdown Voltage (V _{GS} =0V; I _D =1mA)	V _{DSS}	65	70		V
Zero Gate Voltage Drain Leakage Current (V _{DS} = 28 V, V _{GS} = 0 V)	I _{DSS}			10	μA
Gate--Source Leakage Current (V _{GS} = 10 V, V _{DS} = 0 V)	I _{GSS}			1	μA
Gate Threshold Voltage (V _{DS} = 28V, I _D = 600 μA)	V _{GS(th)}		1.8		V
Gate Quiescent Voltage (V _{DD} = 28 V, I _{DQ} = 800 mA, Measured in Functional Test)	V _{GS(Q)}	2.2	2.7	3.2	V

Functional Tests (In Innogrator demo, 50 ohm system) :V_{DD} = 28 Vdc, I_{DQ} = 900 mA, f = 2400 MHz, Pulse CW, Pulse Width=100 μs, Duty cycle=20% .

Power Gain	G _p		18.7		dB
1 dB Compression Point	P _{-1dB}		50.1		dBm
3dB Compression Point	P _{-3dB}		51.0		dBm
Drain Efficiency@P3dB	η _D		54.0		%
Input Return Loss	IRL		-7		dB

Load Mismatch (In Innogrator Test Fixture, 50 ohm system): V_{DD} = 28 Vdc, I_{DQ} = 900 mA, f = 2400 MHz

VSWR 10:1 at 120W pulse CW Output Power	No Device Degradation
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TYPICAL CHARACTERISTICS

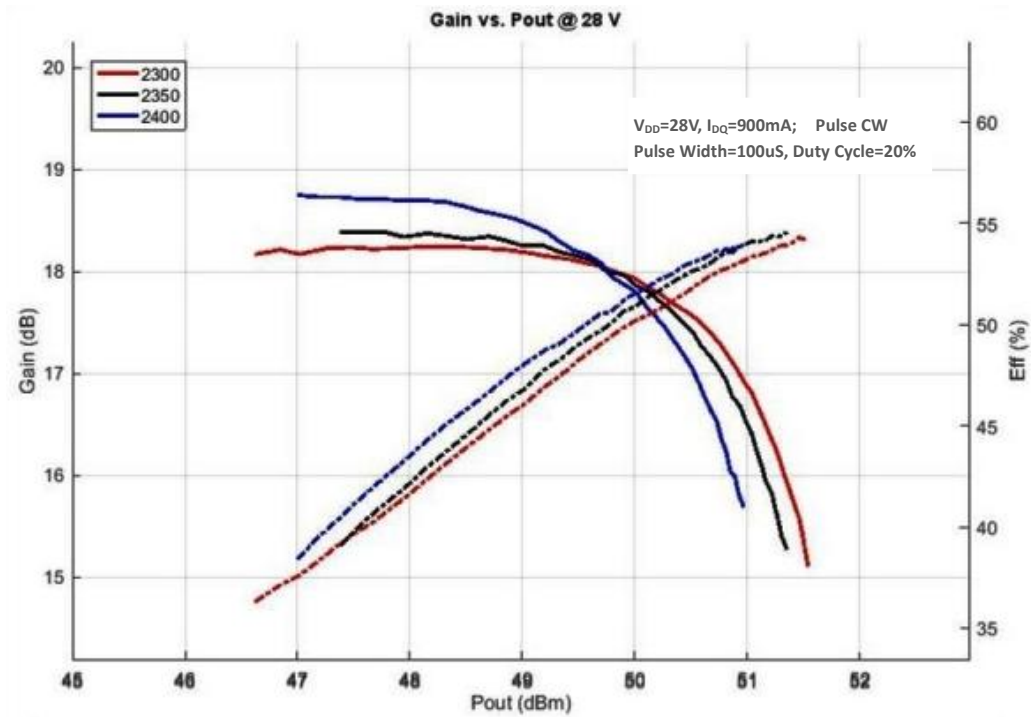
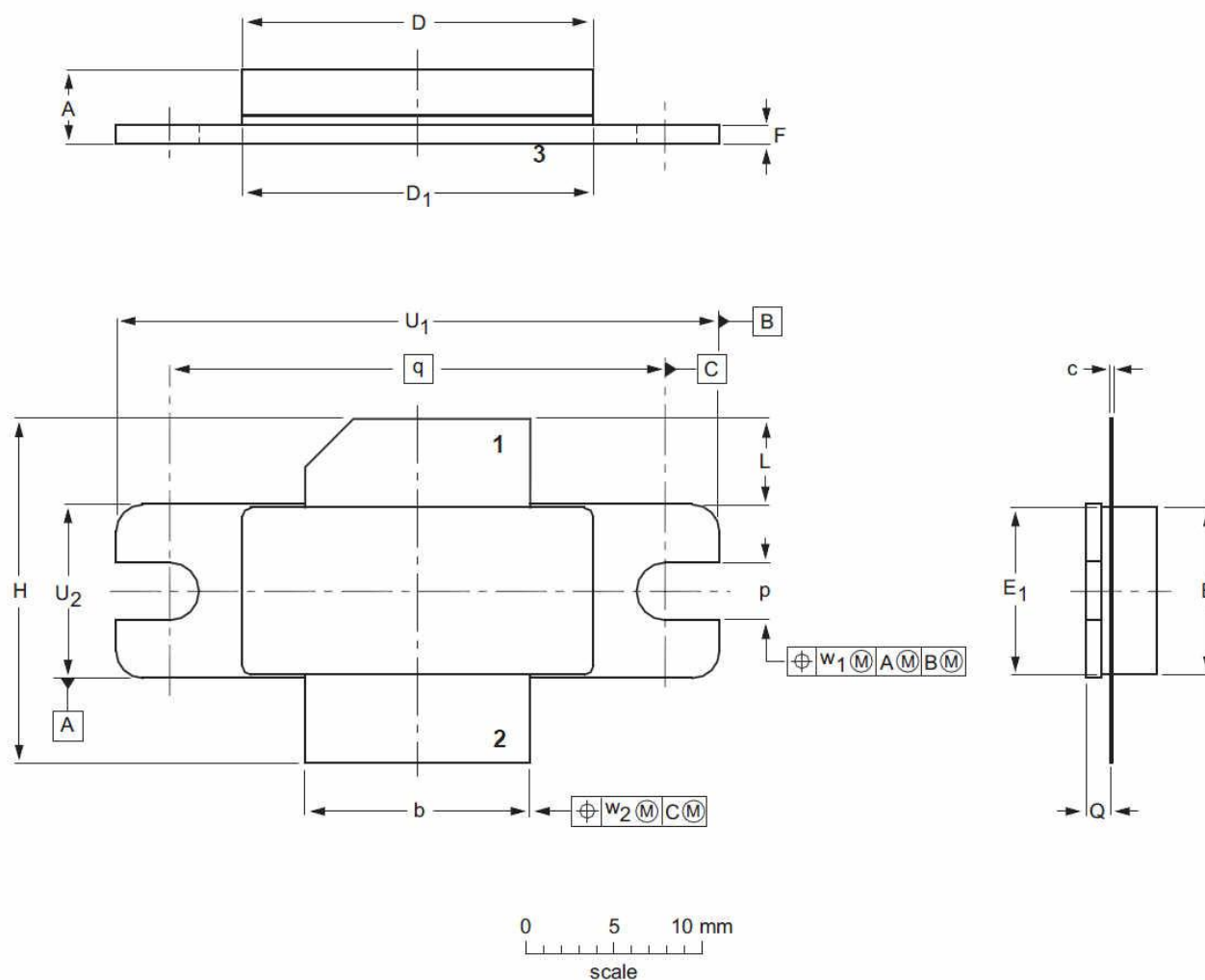


Figure 1. Power gain and drain efficiency as function of
Pulse output power



Package Outline

Flanged ceramic package; 2 mounting holes; 2 leads (1—DRAIN、2—GATE、3—SOURCE)

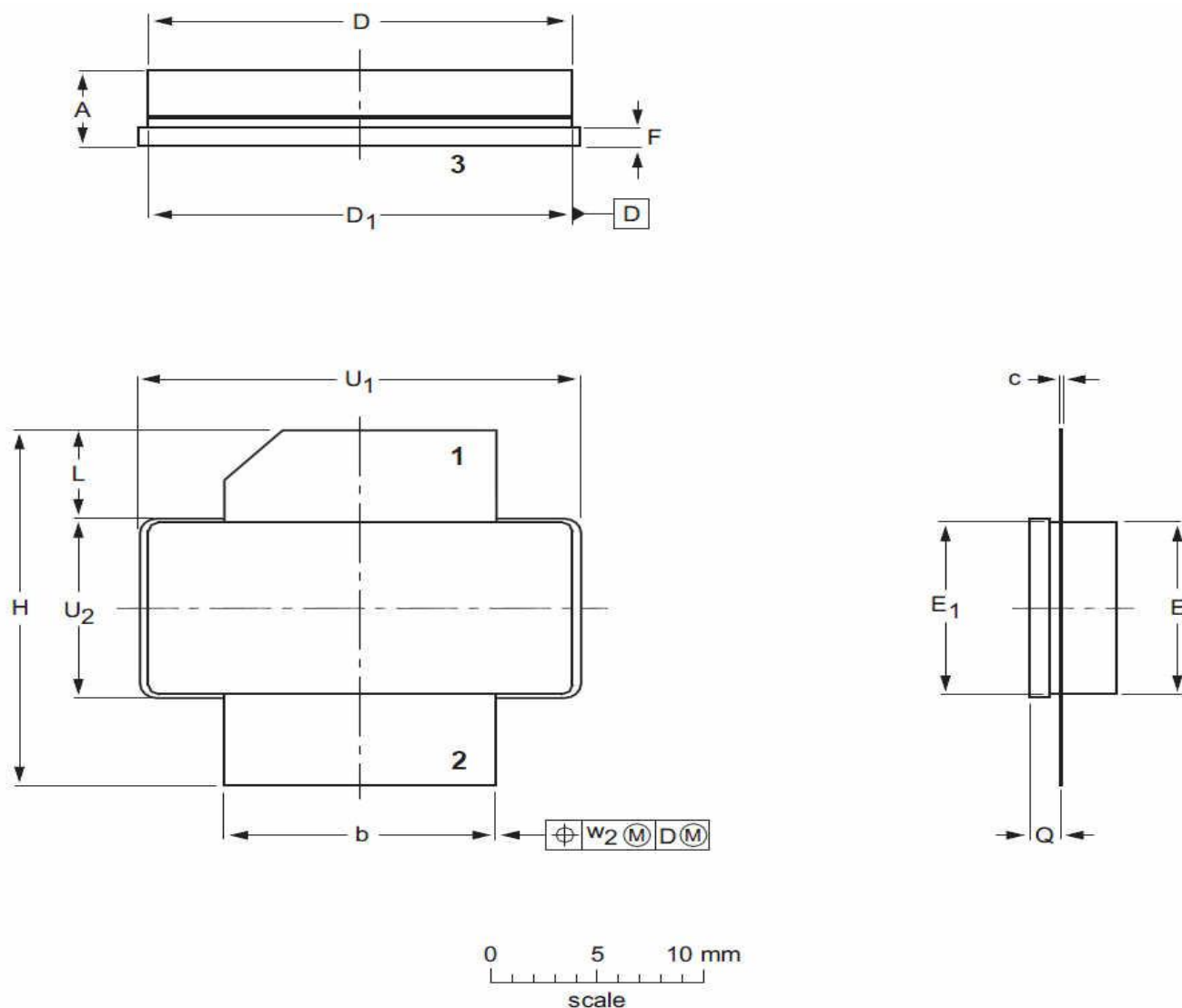


UNIT	A	b	c	D	D ₁	E	E ₁	F	H	L	p	Q	q	U ₁	U ₂	W ₁	W ₂
mm	4.72	12.83	0.15	20.02	19.96	9.50	9.53	1.14	19.94	5.33	3.38	1.70	27.94	34.16	9.91	0.25	0.51
	3.43	12.57	0.08	19.61	19.66	9.30	9.25	0.89	18.92	4.32	3.12	1.45		33.91	9.65		
inches	0.186	0.505	0.006	0.788	0.786	0.374	0.375	0.045	0.785	0.210	0.133	0.067	1.100	1.345	0.390	0.01	0.02
	0.135	0.495	0.003	0.772	0.774	0.366	0.364	0.035	0.745	0.170	0.123	0.057		1.335	0.380		

OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-B2E					03/12/2013



Earless flanged ceramic package; 2 leads (1—DRAIN、2—GATE、3—SOURCE)



UNIT	A	b	c	D	D ₁	E	E ₁	F	H	L	Q	U ₁	U ₂	W ₂
mm	4.72	12.83	0.15	20.02	19.96	9.50	9.53	1.14	19.94	5.33	1.70	20.70	9.91	0.25
	3.43	12.57	0.08	19.61	19.66	9.30	9.25	0.89	18.92	4.32	1.45	20.45	9.65	
inches	0.186	0.505	0.006	0.788	0.786	0.374	0.375	0.045	0.785	0.210	0.067	0.815	0.390	0.010
	0.135	0.495	0.003	0.772	0.774	0.366	0.364	0.035	0.745	0.170	0.057	0.805	0.380	

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PKG-B2					03/12/2013



Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2017/09/01	Rev 1.0	Preliminary Datasheet

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